Product Overview

NTHL080N120SC1A: Silicon Carbide MOSFET, N-Channel, 1200 V, 80 mΩ , TO247-3L

For complete documentation, see the data sheet.

Silicon Carbide (SiC) MOSFET uses a completely new technology that provide superior switching performance and higher reliability compared to Silicon. In addition, the low ON resistance and compact chip size ensure low capacitance and gate charge. Consequently, system benefits include highest efficiency, faster operation frequency, increased power density, reduced EMI, and reduced system size.

Features

- High Speed Switching and Low Capacitance
- 1200V rated
- Max RDS(on) = 110mΩ at Vgs = 20V, Id = 20A
- 100% UIL Tested

Benefits

- Coss = 80pF

Applications

- PFC
- Boost Inverter
- PV Charging

End Products

- Solar Inverter
- Network Power Supply
- Server Power Supply

Part Electrical Specifications

Product	Pricing ($/Unit)	Compliance	Status	Channel Polarity	Configuration	Blocking Voltage BV_{DSS} (V)	$I_{D(max)}$ (A)	$R_{DS(on)}$ Typ @ 25°C (mΩ)	Q_g Total (C)	Output Capacitance (C)	T_j Max (°C)	Package Type
NTHL080N120SC1A	5.9999	Pb-free Halide free	NEW	N-Channel	Single	1200	31	80	56	80	175	TO-247-3LD

For more information please contact your local sales support at www.onsemi.com.

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